LSIC2SD120E30CC



Circuit Diagram TO-247-3L



Description

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. This diode series is ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

Features

- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability

Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Solar inverters

diodes

Pio

• Extremely fast,

temperature-independent

switching behavior

• Dramatically reduced

compared to Si bipolar

switching losses

Industrial motor drives

H F RoHS 🕅

- EV charging stations
- Uninterruptible power supplies

Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = **HF** Halogen Free
- Littelfuse "Pb-free" logo = Pb-free lead plating

Characteristics	Symbol	Conditions	Value	Unit	
Repetitive Peak Reverse Voltage	V _{RRM}	-	1200	V	
DC Blocking Voltage	V _R	T _J = 25 °C	1200	V	
Continuous Forward Current (Per Leg/Component)		T _c = 25 °C	44/88		
	I _F	T _c = 135 °C	21/42	A	
		$T_c = 152^{\circ}C$	15/30		
Non-Repetitive Forward Surge Current (Per Leg)	I _{FSM}	$T_c = 25 \text{ °C}, T_p = 10 \text{ ms}, \text{ Half sine pulse}$	120	А	
Power Dissipation	D	$T_c = 25 \text{ °C}$	214/428	- W	
(Per Leg/Component)	P _{Tot}	T _c = 110 °C	93/186		
Operating Junction Temperature	T	-	-55 to 175	°C	
Storage Temperature	T _{stg}	-	-55 to 150	°C	
Soldering Temperature	T _{sold}	-	260	°C	

Electrical Characteristics (Per Leg)

Characteristics Symb	Question	Conditions	Value			11	
	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Forward Voltage		I _F = 15 A, T _J = 25 °C	-	1.5	1.8	- v	
	V _F	I _F = 15 A, Τ _J = 175 °C	-	2.2	-		
Reverse Current	I _R -	V _R = 1200 V , T _J = 25 °C	-	<1	100	-μA	
		V _R = 1200 V , T _J = 175 °C	-	10			
Total Capacitance		V _R = 1 V, f =1 MHz	-	920	-		
	С	V _R = 400 V, f = 1 MHz	-	88	-	pF	
	_	V _R = 800 V, f = 1 MHz	-	64	-		
otal Capacitive Charge	Q _c	$V_{R} = 800 \text{ V}, Q_{c} = \int C(\text{V}) d\text{V}$	-	92	-	nC	

Footnote: $T_J = +25 \text{ °C}$ unless otherwise specified

Thermal Characteristics							
Characteristics	Symbol	Conditions	Value			Unit	
	Symbol	conditions	Min.	Тур.	Max.	Onit	
Thermal Resistance (Per Leg/Component)	R _{ejc}	-	-	0.70/0.35	-	°C/W	

Figure 1: Typical Foward Characteristics (Per Leg)



Figure 2: Typical Reverse Characteristics (Per Leg)









Figure 5: Capacitance vs. Reverse Voltage (Per Leg)



Figure 7: Stored Energy vs. Reverse Voltage (Per Leg)



Figure 4: Current Derating (Per Leg)



Figure 6: Capacitive Charge vs. Reverse Voltage (Per Leg)



Figure 8: Transient Thermal Impedance (Per Component)



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GEN2 SiC Schottky Diode LSIC2SD120E30CC, 1200 V, 30 A, TO-247-3L

Package Dimensions TO-247-3L





Recommended Hole Pattern Lavout



Notes: 1. Dimensions are in millimeters 2. Dimension D, E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These measured

2. Differentiation 0, L to the include induct match which near shall not exceed 0.127 mm per side. These measured at the outermost extreme of plastic body.
3.øP to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 0.154"

	Millimeters					
Symbol	Min	Nom	Max			
А	4.80	5.03	5.20			
A1	2.25	2.38	2.54			
A2	1.85	1.98	2.11			
b	0.99	-	1.40			
b2	1.65	-	2.39			
b4	2.59	-	3.43			
С	0.38	0.64	0.89			
D	20.80	20.96	21.34			
D1	13.50	-	-			
D2	0.51	1.19	1.35			
е	5.44 BSC					
E	15.75	15.90	16.13			
E1	13.06	14.02	14.15			
E2	4.19	4.32	4.83			
L	19.81	20.19	20.57			
L1	3.81	4.19	4.45			
øP	3.55	3.61	3.66			
øP1	7.06	7.19	7.32			
٥	5.49	5.61	6.20			
S	6.05	6.17	6.30			

Part Numbering and Marking System

SIC

2 SD

120

Е

30

CC YY

WW

Х



- = SiC = Gen2
- = Schottky Diode
- = Voltage Rating (1200 V)
- = TO-247-3L
- = Current Rating (30 A)
- = Common Cathode
- = Year
- = Week
- = Trace Code (Any Letter)
- ZZZZZZ-ZZ = Lot Number

 Packing Options

 Part Number
 Marking
 Packing Mode

 LSIC2SD120E30CC
 SIC2SD120E30CC
 (30pcs)

M.O.Q

450



GEN2 SiC Schottky Diode LSIC2SD120E30CC, 1200 V, 30 A, T0-247-3L

Packing Specification TO-247-3L



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